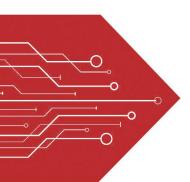
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet







BC846W/BC847W/BC848W





- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

SOT-323

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

P/N MARK

BC846AW=1A; BC846BW=1B;

BC847AW=1E; BC847BW=1F; BC847CW=1G; BC848AW=1J; BC848BW=1K: BC848CW=1L

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{CBO}	Collector-Base Voltage	BC846W	80	
		BC847W	50	V
		BC848W	30	
V _{CEO}	Collector-Emitter Voltage	BC846W	65	
		BC847W	45	V
		BC848W	30	
V _{EBO}	Emitter-Base Voltage	BC846W	6	
		BC847W	6	V
		BC848W	5	
lc	Collector Current –Continuous		0.1	А
Pc	Collector Power Dissipation		150	mW
R _{OJA}	Thermal Resistance From Junction To Ambient		833	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range		-55-150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

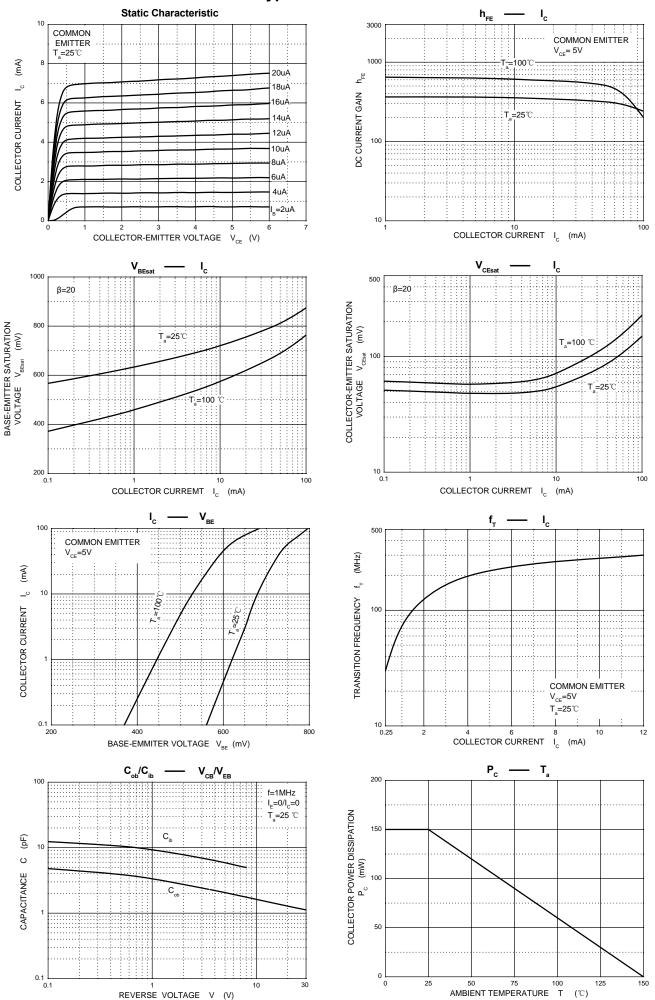
Parameter		Symbol	Test conditions	Min	Тур	[·] Max	Unit
Collector-base breakdown voltage Be	C846W			80			
ВС	C847W	V_{CBO}	$I_{C}=10\mu A, I_{E}=0$	50			V
ВС	C848W			30			
Collector-emitter breakdown voltage BC846W				65			
ВС	C847W	V_{CEO}	$I_C= 10mA, I_B=0$	45			V
ВС	C848W			30			
Emitter-base breakdown voltage BC	C846W			6			
ВС	C847W	V_{EBO}	$I_E = 1 \mu A, I_C = 0$	6			V
ВС	C848W			5			
Collector Cutoff Current		I_{CBO}	V _{CB} =30V			15	nA
DC current gain BC846AW,847AW,8	848AW				90		
BC846BW,847BW,8	48BW	h_FE	V_{CE} = 5V, I_{C} = 10 μ A		150		
BC847CW,BC8	348CW				270		
BC846AW,847AW,	848AW			110		220	
BC846BW,847BW,	848BW		$V_{CE}=5V$, $I_{C}=2mA$	200		450	
BC847CW,BC	848CW			420		800	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =10mA, I _B =0. 5mA			0.25	V
			$I_C=100$ mA, $I_B=5$ mA			0.6	V
Base-emitter saturation voltage		$V_{BE(sat)}$	I _C =10mA, I _B =0. 5mA		0.7		V
			$I_C=100$ mA, $I_B=5$ mA		0.9		V
Base-emitter voltage		V _{BE(on)}	$V_{CE}=5V$, $I_{C}=2mA$	580	660	700	mV
			$V_{CE}=5V$, $I_{C}=10mA$			770	1117
Transition frequency		f⊤	V _{CE} = 5 V, I _C = 10mA	100		_	MHz
			f=100MHz	100			IVITIZ
Collector output capacitance		Cob	V _{CB} =10V,f=1MHz			4.5	pF
Noise figure BC846AW,847AW,	848AW		V _{CE} =5V,I _c =0.2mA,			F€	
BC846BW,847BW,	848BW	NF	f=1KHz,R _S =2KΩ			10	dB
BC847CW,BC	848CW		BW=200Hz			4	



Semiconductor

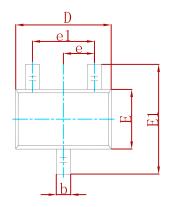
Compiance

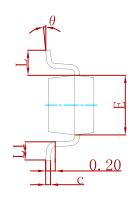
Typical Characteristics

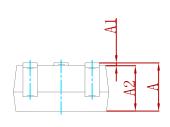




PACKAGE MECHANICAL DATA

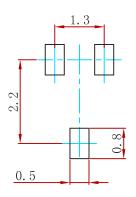






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	A 0.900 1.100		0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BC846W/BC847W/BC848W	SOT-323	3000



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